AMENDMENTS TO THE CLAIMS

Claim 1 (Currently Amended): A method of fabricating a semiconductor device, comprising ~~the step of~~:

forming a source and a drain respectively doped with a first conductivity type in ~~an~~ each active area on both ~~side~~ sides of each word line ~~and by a isolation layer of~~ over a second conductivity type doped substrate, wherein each word line is separated by a predetermined interval;

forming a first contact hole and a second contact hole by using isolation layers which are separated by an interval, which is wider in ~~the~~ each source than in ~~the~~ each drain, to expose the source and the drain; and

selectively implanting a second conductivity type dopant ion in the source by using ~~the~~ each isolation layer and each word line as an ion implanting mask during a tilt ion implantation process.

Claim 2 (Original): The method as recited in claim 1, wherein the tilt ion implantation process is carried out using a tilt angle of about 20° to about 25°.

Claim 3 (Currently Amended): The method as recited in claim 2, wherein the tilt ion implantation process is carried out using ~~a twist~~the tilt angle of about 7° to about 18°.

Claim 4 (Currently Amended): The method as recited in claim 3, wherein the tilt ion implantation process is carried out in a ~~perpendicular to~~ direction of the word line.

Claim 5 (Original): The method as recited in claim 1, wherein the first conductivity type is N-type and the second conductivity type is P-type.

Claim 6 (Currently Amended): The method ~~of fabricating the semiconductor device~~ as recited in claim 5, the second conductivity type dopant ion is a Boron.